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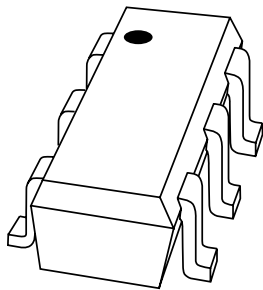
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via [salesaddresses@nexperia.com](mailto:salesaddresses@nexperia.com)). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# DATA SHEET



## **PUMZ1** NPN/PNP general purpose transistors

Product data sheet  
Supersedes data of 2002 May 6

2004 Oct 15

# NPN/PNP general purpose transistors

# PUMZ1

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and boardspace.

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

Two independently operating NPN/PNP transistors in an SC-88; SOT363 plastic package.

### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PUMZ1	F*Z

### Note

- \* = -: Made in Hong Kong.  
 \* = t: Made in Malaysia.  
 \* = W: Made in China.

### ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PUMZ1	–	plastic surface mounted package; 6 leads	SOT363

### PINNING

PIN	DESCRIPTION	
1, 4	emitter	TR1; TR2
2, 5	base	TR1; TR2
3, 6	collector	TR2; TR1

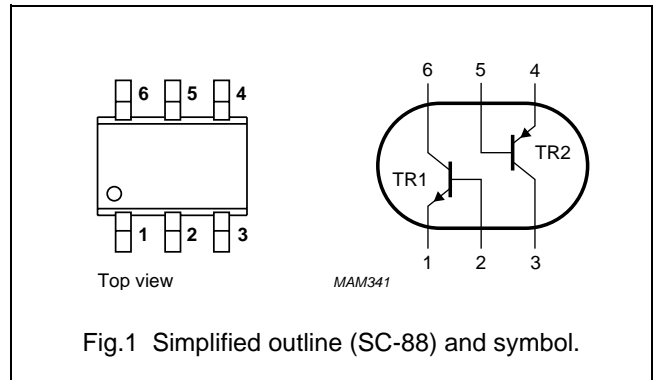


Fig.1 Simplified outline (SC-88) and symbol.

## NPN/PNP general purpose transistors

PUMZ1

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor; for the PNP transistor with negative polarity</b>					
V <sub>CBO</sub>	collector-base voltage	open emitter	–	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	5	V
I <sub>C</sub>	collector current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	200	mA
I <sub>BM</sub>	peak base current		–	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	–	200	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C
<b>Per device</b>					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	300	mW

**Note**

1. Device mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
<b>Per device</b>				
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	416	K/W

**Note**

1. Device mounted on an FR4 printed-circuit board.

## NPN/PNP general purpose transistors

## PUMZ1

**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor; for the PNP transistor with negative polarity</b>					
$I_{CBO}$	collector-base cut-off current	$I_E = 0\text{ A}; V_{CB} = 30\text{ V}$	–	100	nA
		$I_E = 0\text{ A}; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	10	$\mu\text{A}$
$I_{EBO}$	emitter-base cut-off current	$I_C = 0\text{ A}; V_{EB} = 4\text{ V}$	–	100	nA
$h_{FE}$	DC current gain	$I_C = 1\text{ mA}; V_{CE} = 6\text{ V}$	120	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 50\text{ mA}; I_B = 5\text{ mA}; \text{note 1}$	–	200	mV
$C_c$	collector capacitance TR1 TR2	$I_E = i_e = 0\text{ A}; V_{CB} = 12\text{ V}; f = 1\text{ MHz}$	–	1.5	pF
			–	2.2	pF
$f_T$	transition frequency	$I_C = 2\text{ mA}; V_{CE} = 12\text{ V}; f = 100\text{ MHz}$	100	–	MHz

**Note**

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .

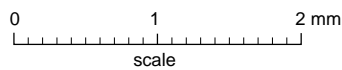
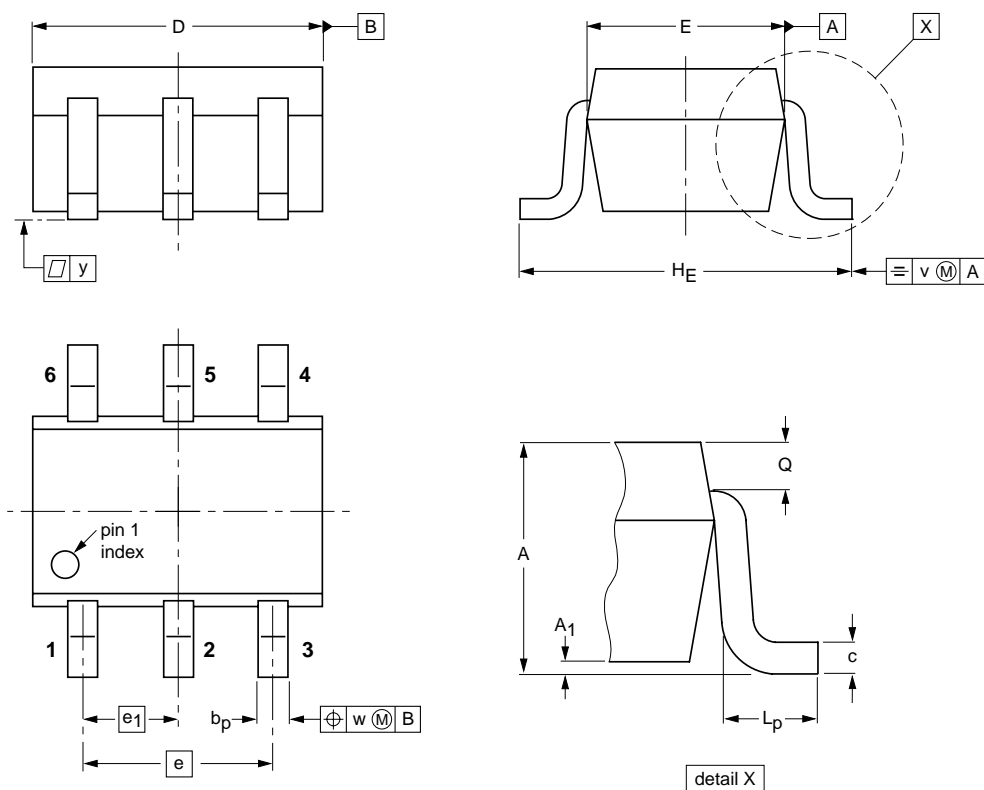
NPN/PNP general purpose transistors

PUMZ1

PACKAGE OUTLINE

Plastic surface-mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			04-11-08 06-03-16

## NPN/PNP general purpose transistors

PUMZ1

## DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

## Notes

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# ***NXP Semiconductors***

## **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

## **Contact information**

For additional information please visit: <http://www.nxp.com>

For sales offices addresses send e-mail to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

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